

NCE N-Channel Enhancement Mode Power MOSFET

DESCRIPTION

The NCE0157 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

GENERAL FEATURES

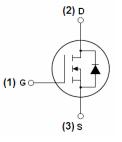
- $V_{DS} = 100V, I_D = 57A$ $R_{DS(ON)} < 23m\Omega @ V_{GS} = 10V (Typ:13.3m\Omega)$
- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

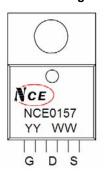
- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin Assignment



TO-220 top view

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0157	NCE0157	TO-220	-	-	-

Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	57	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100°C)	40	Α
Pulsed Drain Current	I _{DM}	190	Α
Maximum Power Dissipation	P _D	200	W
Derating factor		1.61	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	580	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 150	$^{\circ}$



NCE0157

Thermal Characteristic

Electrical Characteristics (TA=25°C unless otherwise noted)

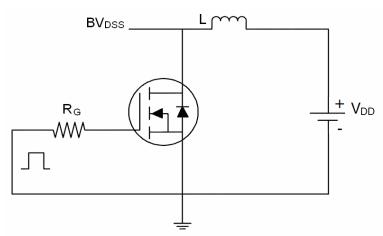
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	•					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V			1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V			±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =28A		13.3	23	mΩ
Forward Transconductance	g FS	V _{DS} =25V,I _D =28A	32			S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}	V 05VV 0V		2700		PF
Output Capacitance	C _{oss}	V _{DS} =25V,V _{GS} =0V,		350		PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz		150		PF
Switching Characteristics (Note 4)	•					
Turn-on Delay Time	t _{d(on)}			12		nS
Turn-on Rise Time	t _r	V _{DD} =50V,I _D =28A		55		nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =2.5 Ω		45		nS
Turn-Off Fall Time	t _f			47		nS
Total Gate Charge	Qg	V 00V/1 00A		95		nC
Gate-Source Charge	Q _{gs}	V _{DS} =80V,I _D =28A,		18		nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V		25		nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =28A		0.85	1.2	V
Diode Forward Current (Note 2)	Is				57	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 28A		140	220	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs(Note3) 650 1000		nC		
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

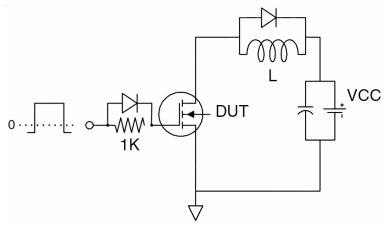
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}\text{C}$,VDD=50V,VG=10V,L=0.5mH,Rg=25 Ω

Test circuit

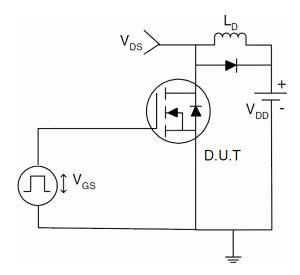
1) E_{AS} test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit:



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

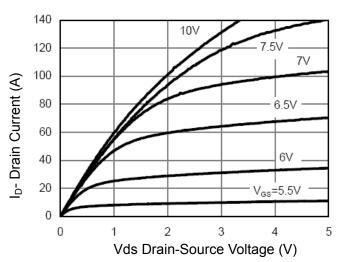


Figure 1 Output Characteristics

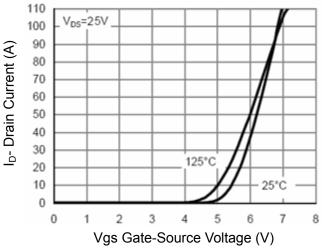


Figure 2 Transfer Characteristics

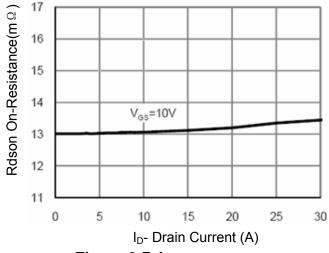


Figure 3 Rdson- Drain Current

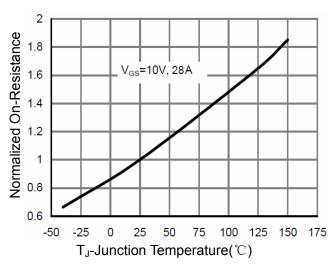


Figure 4 Rdson-JunctionTemperature

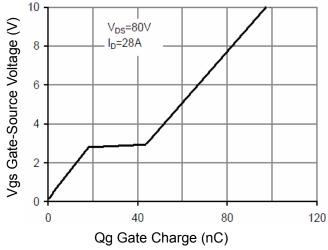


Figure 5 Gate Charge

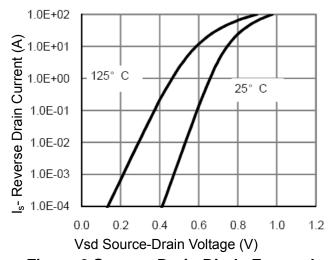
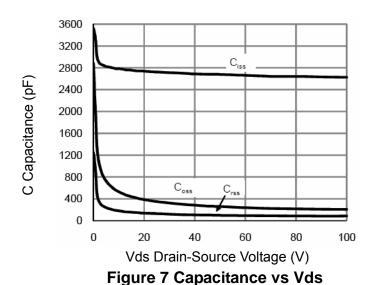


Figure 6 Source- Drain Diode Forward



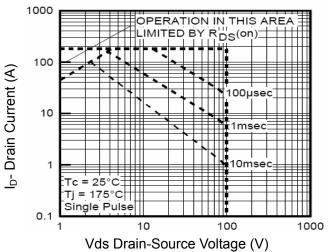


Figure 8 Safe Operation Area

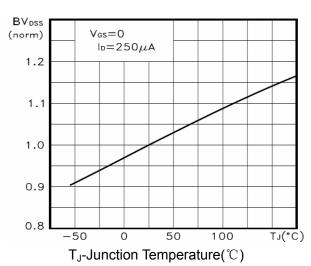


Figure 9 BV_{DSS} vs Junction Temperature

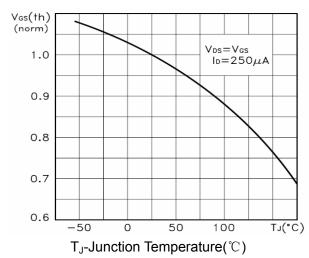


Figure 10 V_{GS(th)} vs Junction Temperatur

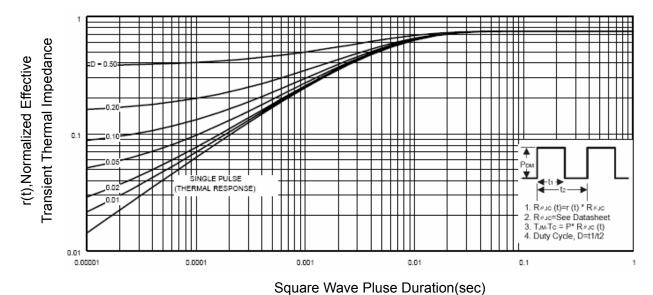
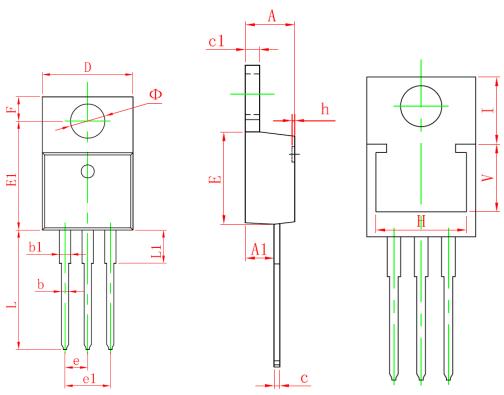


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
A	4.470	4.670	0.176	0.184	
A1	2.520	2.820	0.099	0.111	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
c	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	10.010	10.350	0.394	0.407	
E	8.500	8.900	0.335	0.350	
E1	12.060	12.460	0.475	0.491	
e	2.540 (TYP.)		0.100 (TYP.)		
e1	4.980	5.180	0.196	0.204	
F	2.590	2.890	0.102	0.114	
Н	8.440 REF.		0.332 REF.		
h	0.000	0.300	0.000	0.012	
L	13.400	13.800	0.528	0.543	
L1	3.560	3.960	0.140	0.156	
V	6.360 REF.		0.250 REF.		
I	6.300 REF.		0.248 REF.		
Ф	3.735	3.935	0.147	0.155	

Pb Free Product
NCE0157

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